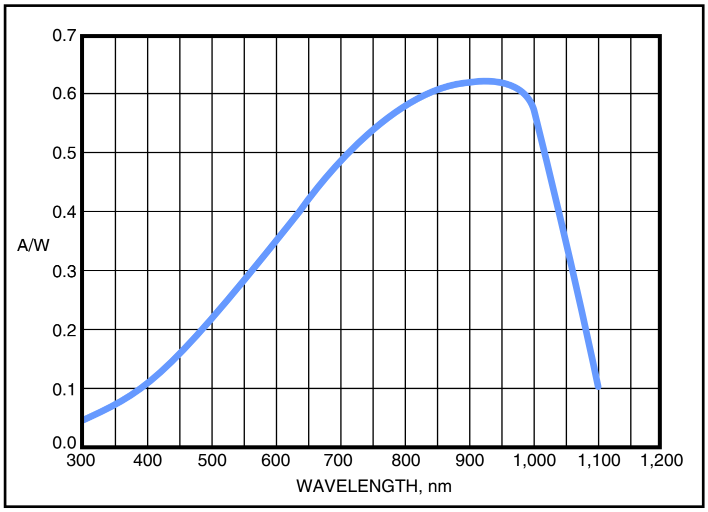
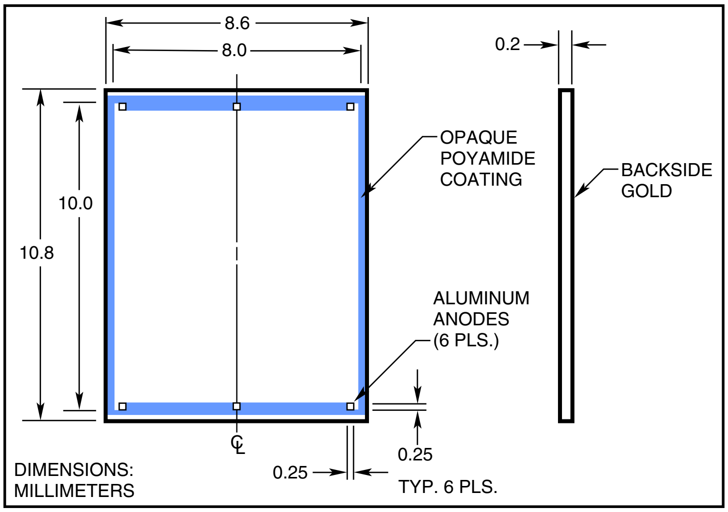
DATA SHEET PSS80-7-C

SILICON PHOTODIODE TYPE PSS80-7-C

PSS80-7-C has an active area of 80 mm^2 and features very low capacitance for its size (45 pF at 12 volts bias). The active area is surrounded by a reflective aluminum stripe that prevents illumination of the so-called “dead” silicon. This improves the speed of response. The die may be mounted in hermetically sealed packages or it is now available in our surface mounting assembly illustrated the next page. (Please see PSS80-7-SM).



SPECTRAL RESPONSE



OUTLINE DIMENSIONS

PHOTODIODE CHARACTERISTICS

PART NO.	ACTIVE AREA mm^2	ACTIVE AREA (size) mm	DARK CURRENT nA @ 12V		CAPACITANCE PF @		RISE TIME @ 663 nm ns @ 12 V	NEP W/H$^{1/2}$ OV@ 663 nm
			TYP	MAX	0V	12V		
PSS80-7-C	80	8 x 10	5	10	135	45	45	5* x10^{-14}

ABSOLUTE MAXIMUM RATINGS

DC REVERSE VOLTAGE	PEAK DC CURRENT	STORAGE TEMPERATURE	OPERATING TEMPERATURE	SOLDERING TEMPERATURE
30	10 mA	–50°C to +130°C	–40°C to 105°C	N/A